Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC5066FT

VHF~UHF Band Low Noise Amplifier Applications

• Low noise figure, high gain.

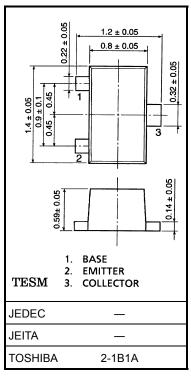
• NF = 1.1dB, $|S_{21e}|^2 = 12dB$ (f = 1 GHz)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	VCEO	12	V
Emitter-base voltage	V _{EBO}	3	V
Base current	Ι _Β	15	mA
Collector current	IC	30	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.0022 g (typ.)

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f _T	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$	5	7	_	GHz
Insertion gain	S _{21e} ² (1)	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}, f = 500 \text{ MHz}$	-	17	_	dB
	S _{21e} ² (2)	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}, f = 1 \text{ GHz}$	8.5	12	_	
Noise figure	NF (1)	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ mA}, f = 500 \text{ MHz}$	_	1	_	dB
	NF (2)	$V_{CE} = 5 \text{ V}, I_{C} = 3 \text{ mA}, f = 1 \text{ GHz}$	_	1.1	2.0	GD.

Electrical Characteristics (Ta = 25°C)

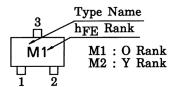
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 10 V, I _E = 0	_	_	1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 1 V, I _C = 0	_	_	1	μА
DC current gain	h _{FE} (Note 1)	V _{CE} = 5 V, I _C = 10 mA	80	_	240	
Output capacitance	C _{ob}	$V_{CB} = 5 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.7	_	pF
Reverse transfer capacitance	C _{re}	VCB = 3 V, IE = 0, I = 1 IMFIZ (NOTE 2)	_	0.45	0.9	pF

Note 1: hFE classification O: 80~160, Y: 120~240

Note 2: Cre is measured by 3 terminal method with capacitance bridge.

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Marking



2 2007-11-01

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20070701-EN GENERAL

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